N-Ch MOSFET

General Description

The WSR3090 is the highest performance trench N-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSR3090meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

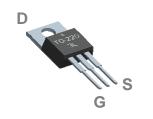
Product Summery

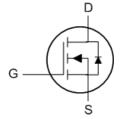
BVDSS	RDSON	ID
30V	$4.5 m\Omega$	90A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

TO-220 Pin Configuration





Absolute Maximum Ratings

		Rating		
Symbol	Parameter	10s	Steady State	Units
V _{DS}	Drain-Source Voltage		30	
V _{GS}	Gate-Source Voltage	<u> </u>	20	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ¹		90	Α
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ¹		60	Α
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	27	17	Α
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	23	14.5	Α
I _{DM}	Pulsed Drain Current ² 160		Α	
EAS	Single Pulse Avalanche Energy ³	Single Pulse Avalanche Energy ³ 252		mJ
I _{AS}	Avalanche Current 48		Α	
P _D @T _C =25℃	Total Power Dissipation ⁴		53	
P _D @T _A =25℃	Total Power Dissipation ⁴	6	2.0	W
T _{STG}	Storage Temperature Range	-55	-55 to 175	
TJ	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹		62	°C/W
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		25	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		2.8	°C/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃, I _D =1mA		0.028		V/°C
D	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		4.5	5.5	0
$R_{DS(ON)}$		V _{GS} =4.5V , I _D =15A		7.8	9	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V V I 050 A	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-6.16		mV/℃
	Drain Source Loakage Current	V_{DS} =24V , V_{GS} =0V , T_J =25 $^{\circ}\mathrm{C}$			1	- uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =55℃			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V_{DS} =5V , I_D =30A		43		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7	3.1	Ω
Qg	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =4.5V , I _D =15A		20	28	
Q_{gs}	Gate-Source Charge			7.6	10.6	nC
Q_{gd}	Gate-Drain Charge			7.2	10.1	
T _{d(on)}	Turn-On Delay Time			11	15.6	
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		15	27	no
T _{d(off)}	Turn-Off Delay Time			37.3	74.6	ns
T _f	Fall Time			10.6	21.2	
Ciss	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		2295		
C _{oss}	Output Capacitance			570		pF
C _{rss}	Reverse Transfer Capacitance			210		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V , L=0.1mH , I _{AS} =24A	63			mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	\\ -\\ -0\\			35	А
I _{SM}	Pulsed Source Current ^{2,6}	V _G =V _D =0V , Force Current			160	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1	V
t _{rr}	Reverse Recovery Time			30		nS
Qrr	Reverse Recovery Charge	IF=30A , dl/dt=100A/ μ s , T $_{J}$ =25 $^{\circ}$ C		24		nC

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10 sec.
- 2.The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$
- 3.The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =24A
- 5. The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.







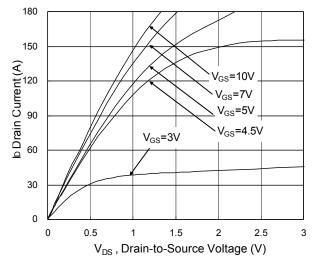


Fig.1 Typical Output Characteristics

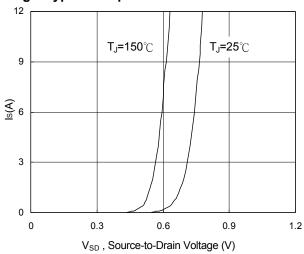


Fig.3 Forward Characteristics of Reverse

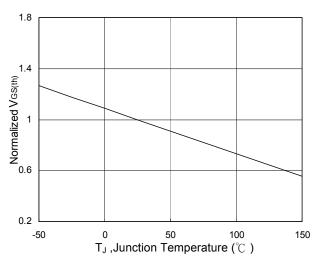


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

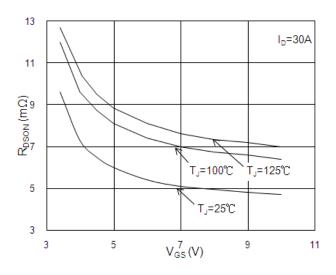


Fig.2 On-Resistance vs. G-S Voltage

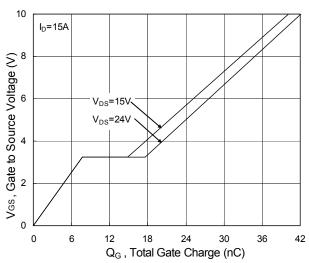


Fig.4 Gate-Charge Characteristics

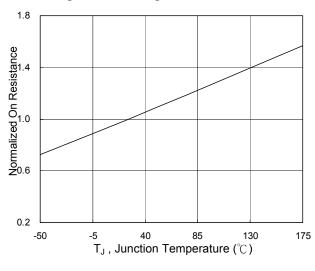
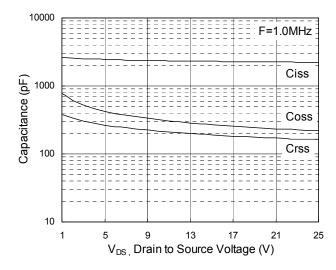


Fig.6 Normalized R_{DSON} vs. T_J







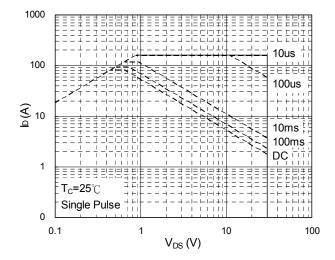


Fig.7 Capacitance

Fig.8 Safe Operating Area

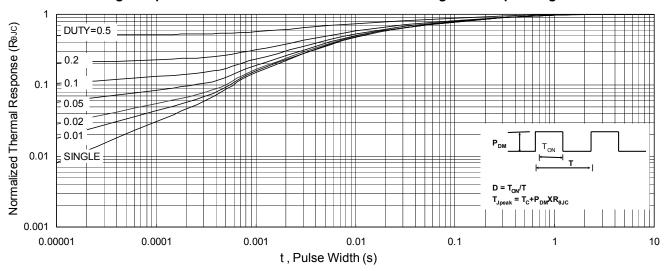


Fig.9 Normalized Maximum Transient Thermal Impedance

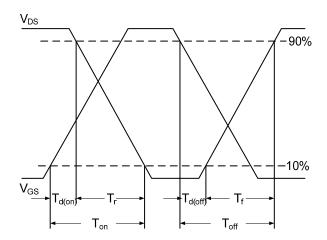


Fig.10 Switching Time Waveform

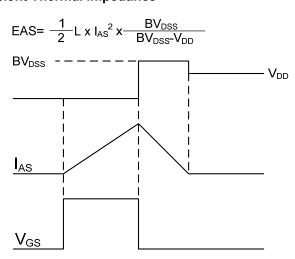


Fig.11 Unclamped Inductive Switching Waveform



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